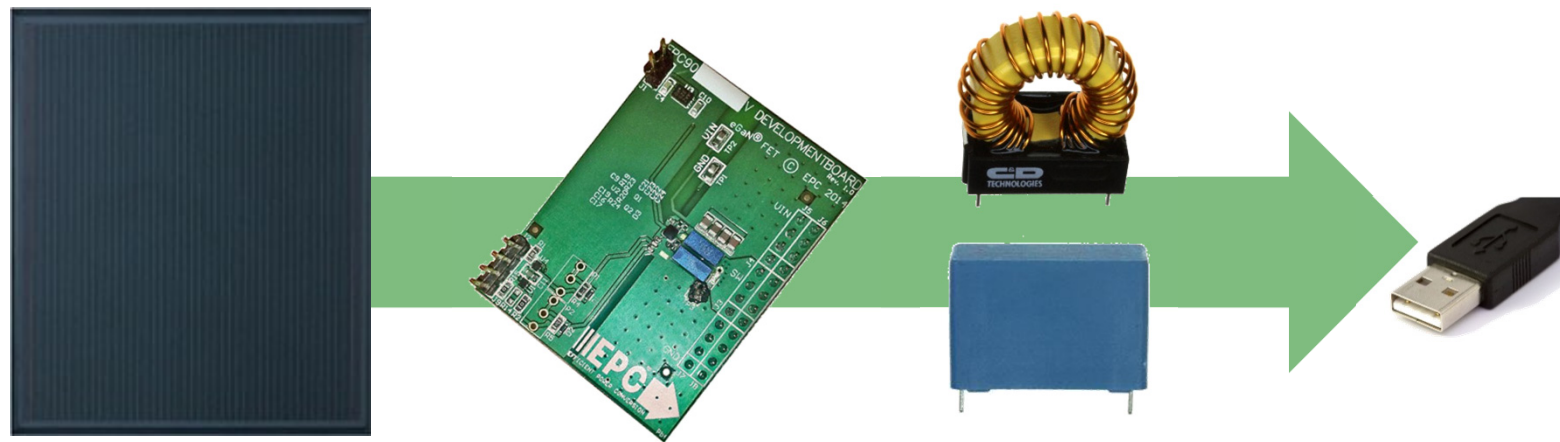


# Announcements

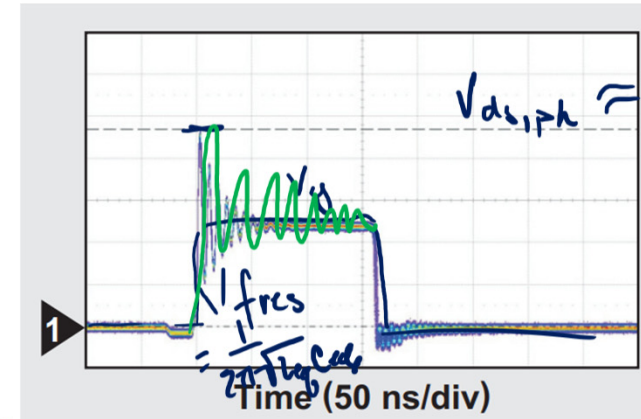
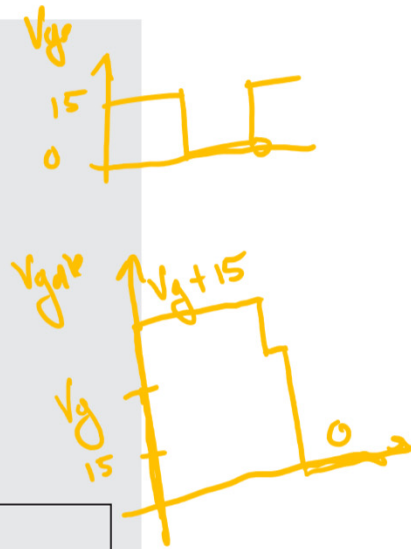
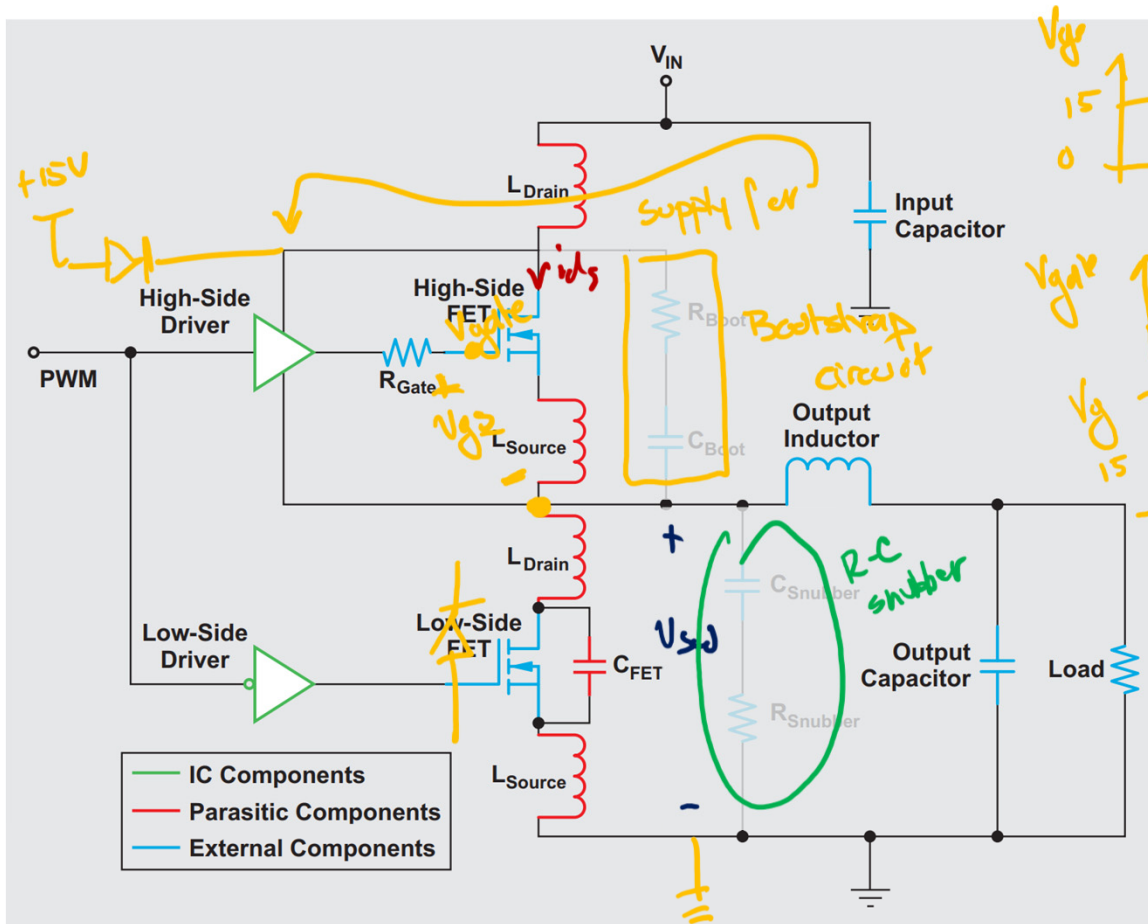
- Experiment 1 assigned
  - Model PV panel for future converter design/analysis
  - Self-assign lab groups of 3 in canvas **this week**
  - Complete experiment next week 9/23-9/27
  - Report due 10/4



# Lab Time

- Experiments performed in MK225
- E-mail Elizabeth Sutton ([esutton4@utk.edu](mailto:esutton4@utk.edu)) to schedule
  - MTWF: 10 am - 2 pm
  - R: 12 pm - 4 pm
  - One e-mail *per group*
- Read through lab and plan your procedure in advance

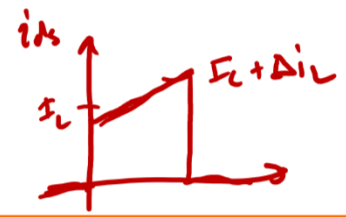
# Experimental Switching Waveforms



(a) Baseline ringing (5 V/div)

$E_{\text{lost}} = \frac{1}{2} L_p I_c^2$   
 all lost if ringing dies out before end of period

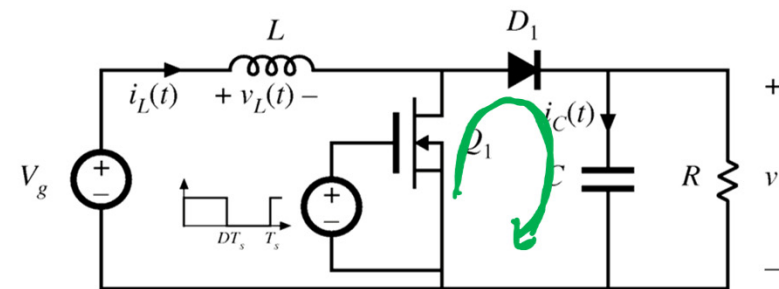
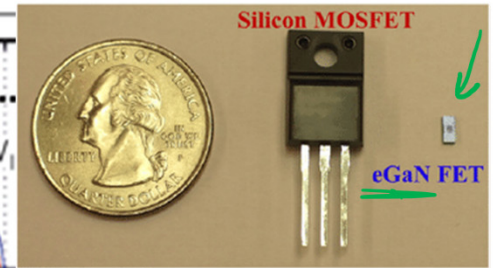
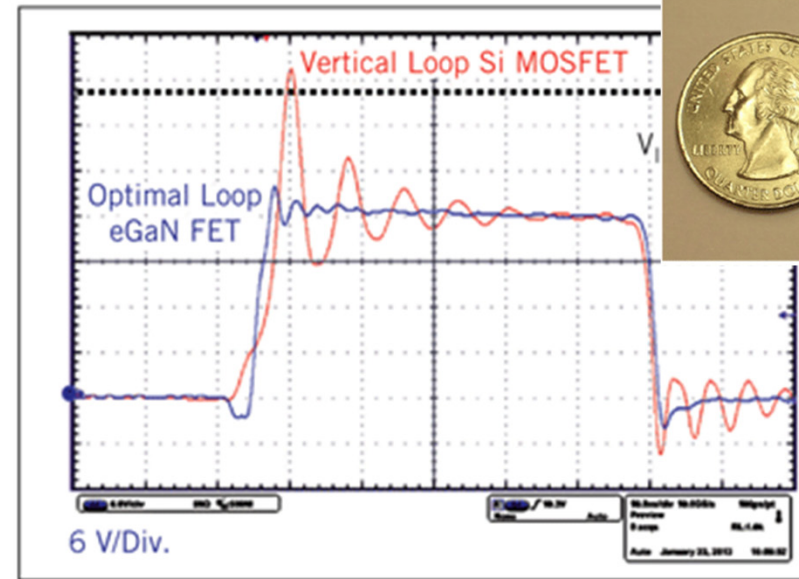
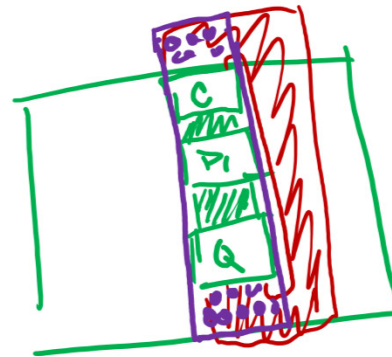
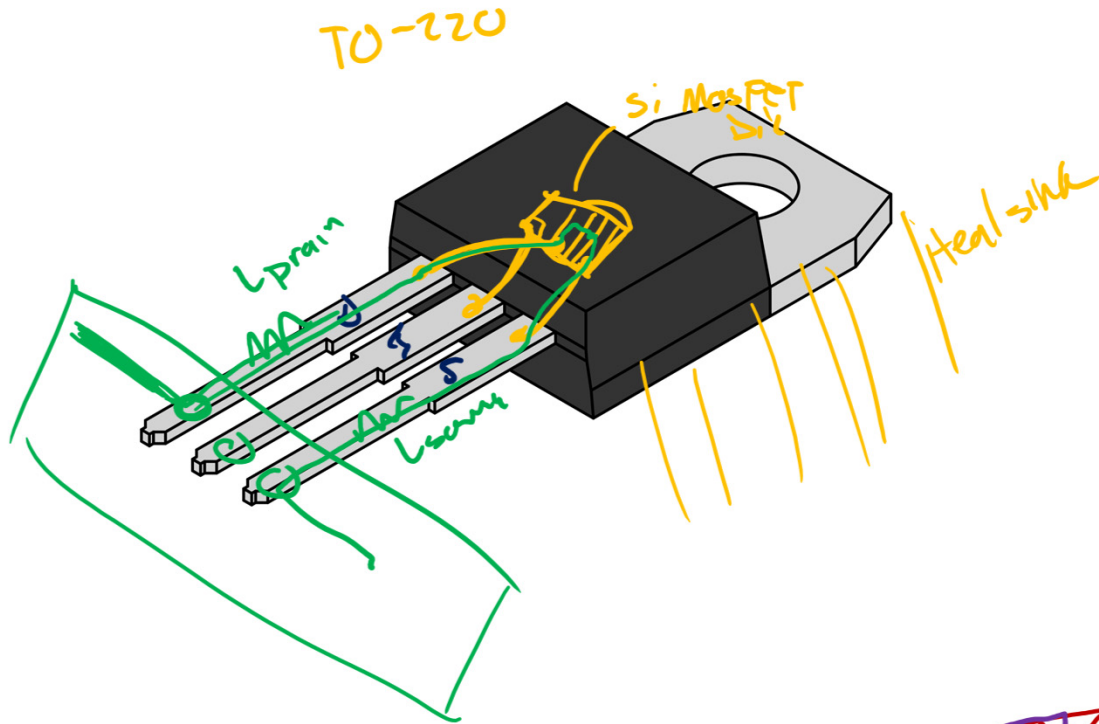
$$P_{\text{sw}} = \frac{1}{2} L_p I_c^2 f_s$$



or

$$\frac{1}{2} L_p (I_c + \Delta i_L)^2 f_s$$

# Device Packaging and Layout



# The Double Pulse Test

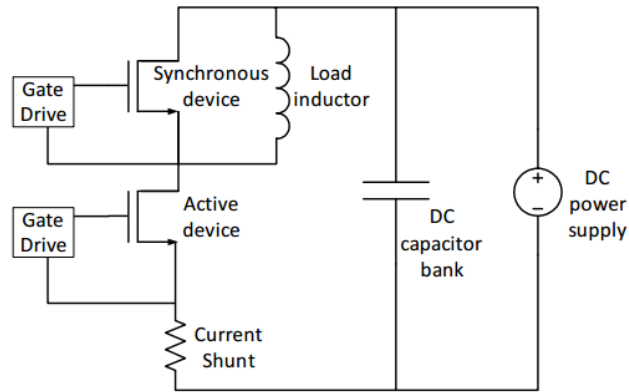


Fig. 7. Double pulse test circuit schematic.

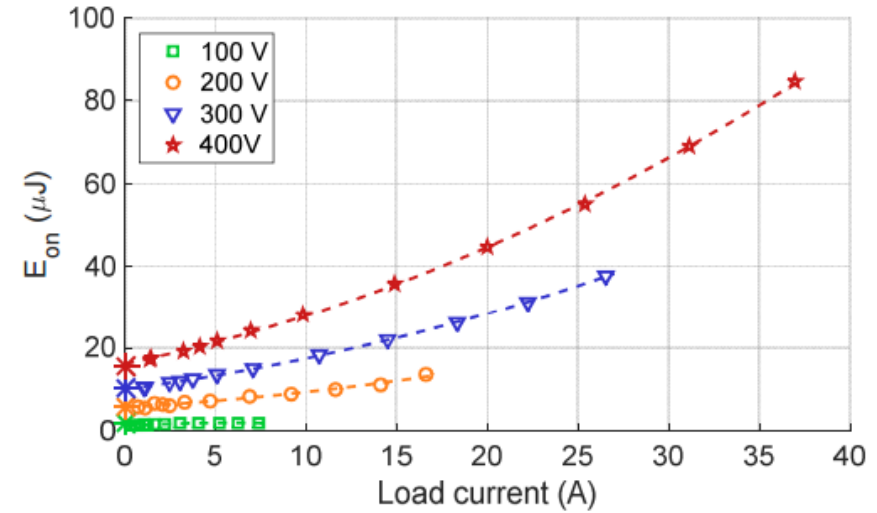
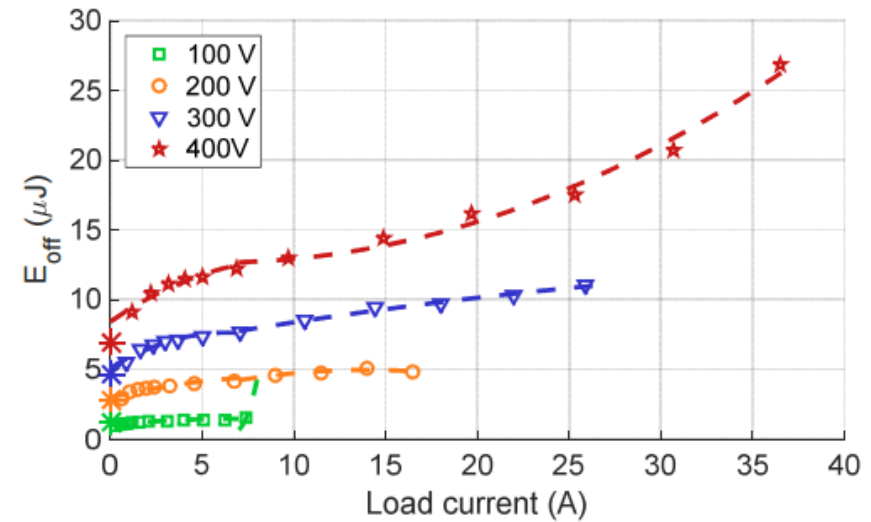
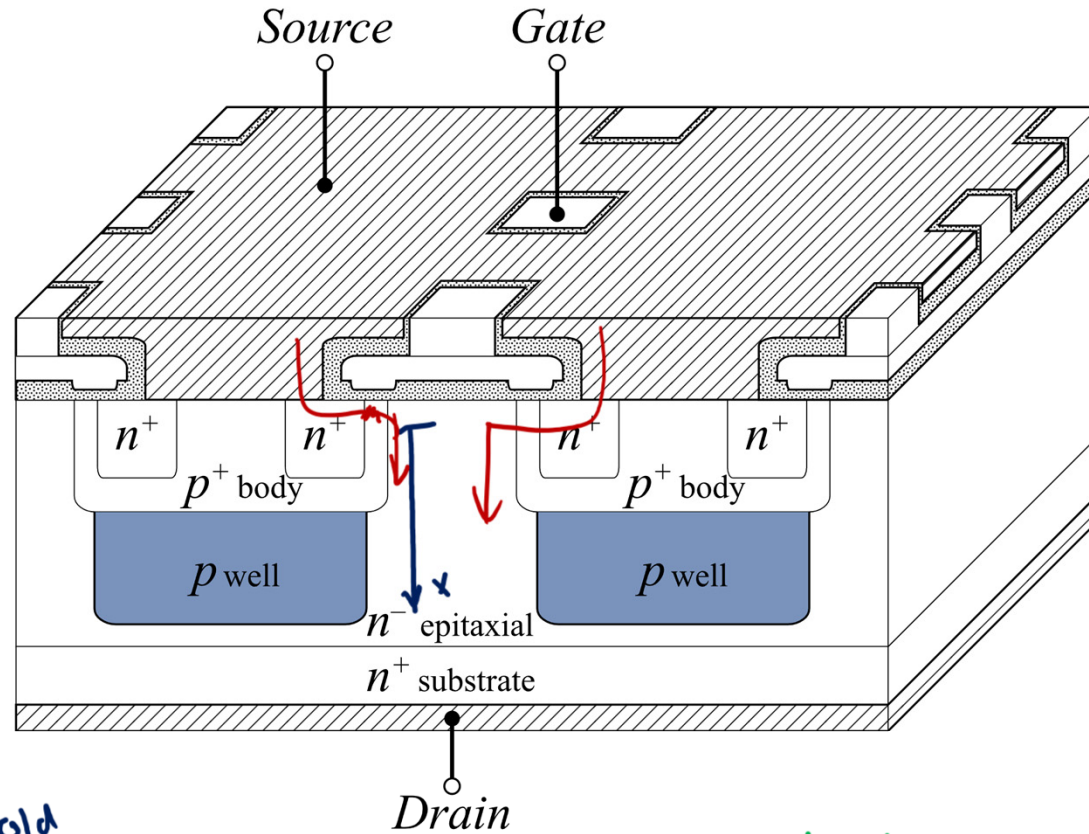


Fig. 16. Turn-on energy  $E_{on}$  at 25 °C.

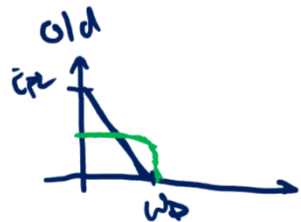
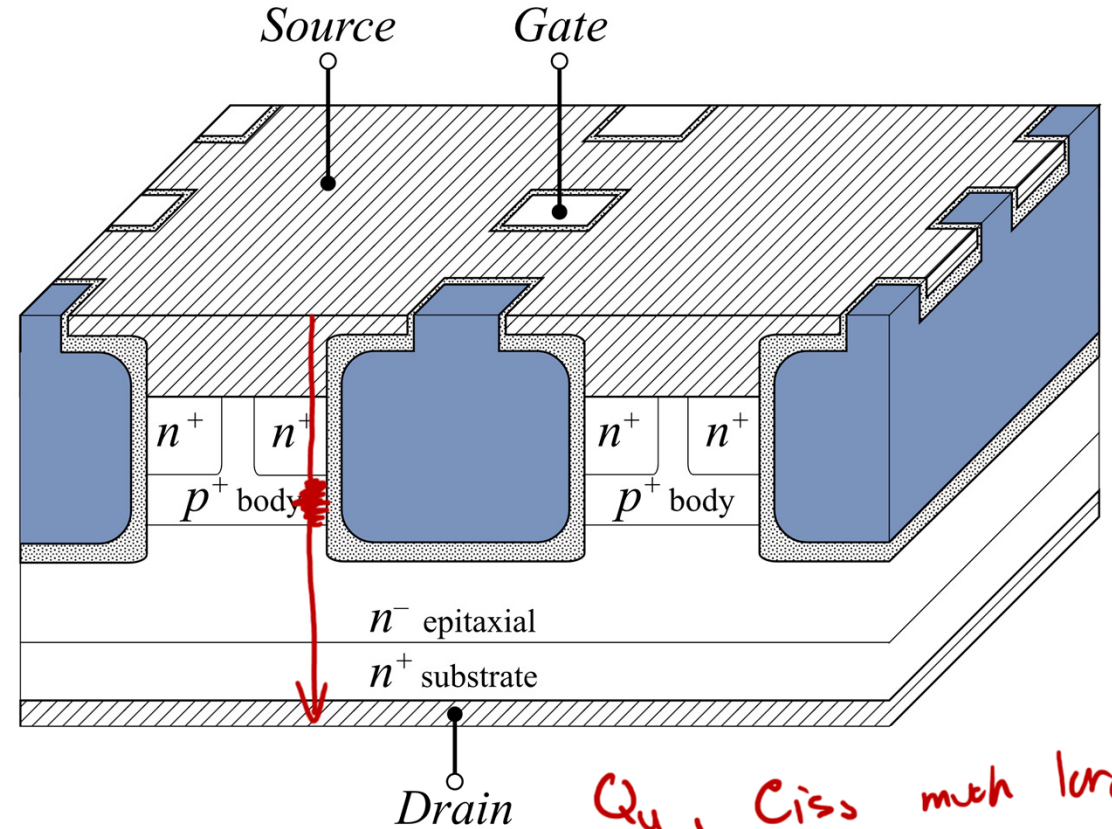


# Other Device Structures

Superjunction



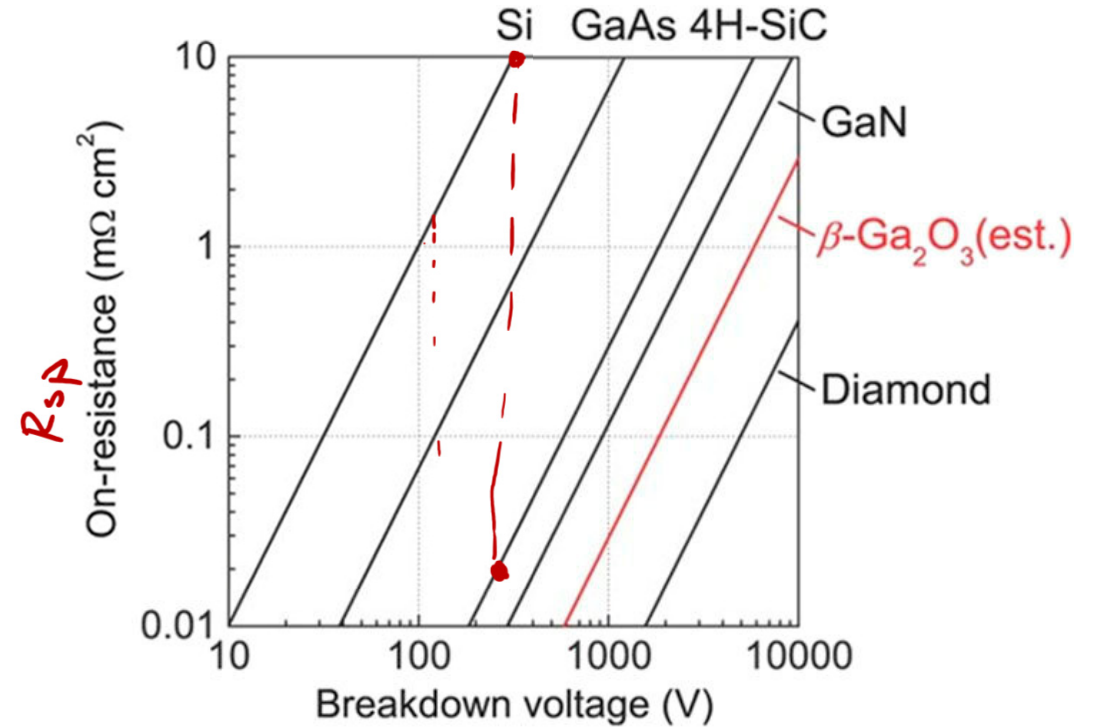
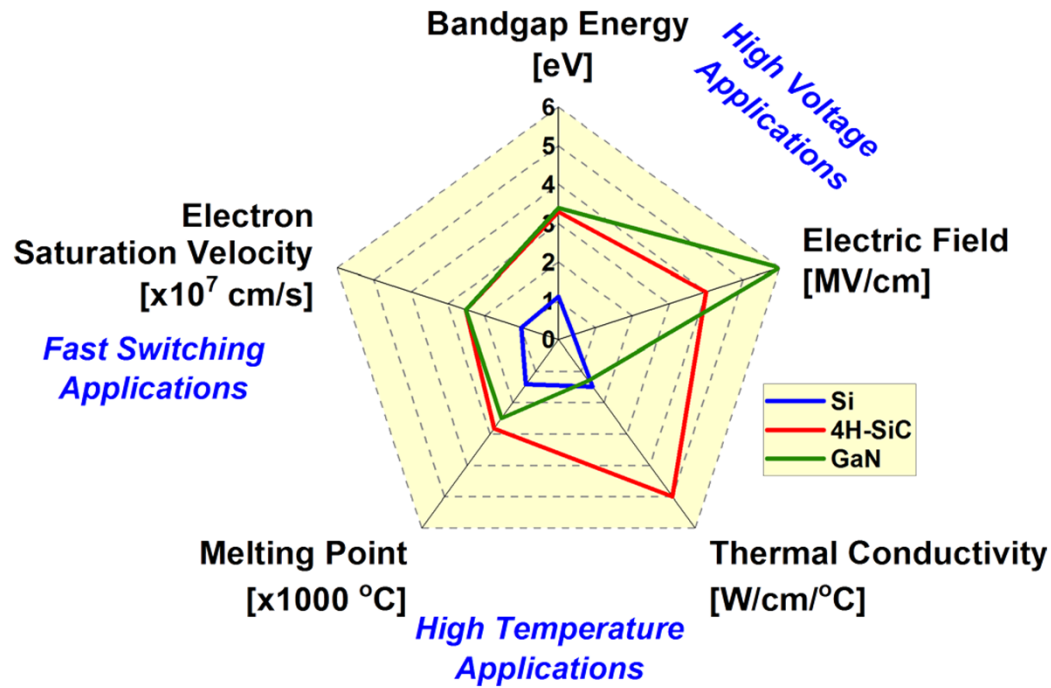
Trench Gate



$R_{sp} \rightarrow k_1 V_{DS}$  instead of  $k_2 V_{DS}^2$

$Q_g, C_{iss}$  much longer  
Lower  $R_{on}$  @ low voltages

# Wide Bandgap Materials



<https://potential.eecs.utk.edu/About.php?topic=PowerSemiconductors>

# GaN HEMTs

gate current not zero  
Not a MOSFET

No body diode

very high reverse conduction loss due to  $V_{th}$  effect

